

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and epitaxy and silicon and porous and transistor and tranducer and microphone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:13
S2	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and tranducer and microphone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:13
S3	554	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:13
S4	2	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and microphone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:13
S5	62	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:13
S6	62	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:14
S7	6	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:14
S8	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (nitrogen near8 atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:14

S9	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon near8 atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:15
S10	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (helium near8 atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:15
S11	36	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:15
S12	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmospher	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:15
S13	29	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:57
S14	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere and epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:15
S15	0	((semiconductor or substrate or wafer or chip) near8 (trench\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere and "SOI"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:44
S16	190	"5324683"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:45

S17	168	"5324683"	USPAT	OR	ON	2005/10/13 08:45
S18	44	((semiconductor or substrate or wafer or chip) near8 (trench\$2 or slot\$2 or hole\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 09:14
S19	1	((semiconductor or substrate or wafer or chip) near8 (trench\$2 or slot\$2 or hole\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere and epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 08:58
S20	29	((semiconductor or substrate or wafer or chip) near8 (trench\$2 or slot\$2 or hole\$2)) and cavity and anneal\$4 and transistor and transducer and (dielectric or oxide) and (argon or nitrogen or xenon or helium) and atmosphere and epitax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 11:47
S21	9508070	DE "10131249" A1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 11:48
S22	0	("DE10131249A1").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:49
S23	0	("DE10131249A1").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:49
S24	0	("10131249A1").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:49
S25	4	("10131249").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:58
S26	0	(2004/0142542A1).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:59

S27	0	2004/0142542	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 11:59
S28	0	"2004/0142542 A1"	US-PGPUB	OR	OFF	2005/10/13 11:59
S29	1	("0142542").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 12:00
S30	0	(2004/0142542).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 12:01
S31	0	(US2004/0142542).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 12:03
S32	2	"20040142542"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 12:36
S33	1	"SOI" and "porous silicon" and (dielectric or oxide) and transistor and microphone and transducer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/10/13 12:38
S34	523	"SOI" and "porous silicon" and (dielectric or oxide) and (transistor or microphone or transducer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 12:38
S35	8	"SOI" and "porous silicon" and (dielectric or oxide) and (transistor and microphone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 12:39
S36	6	"SOI" and "porous silicon" and (dielectric or oxide) and (transistor and transducer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 12:39